

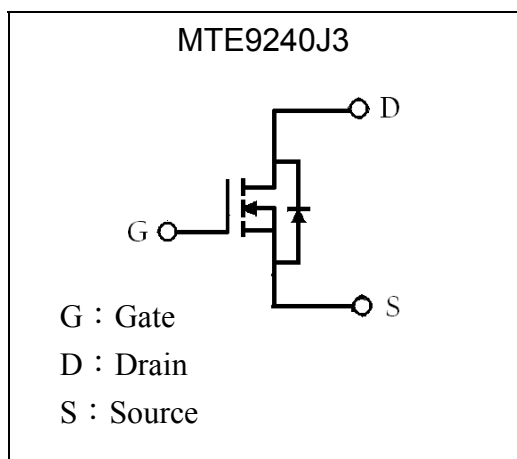
N-Channel Enhancement Mode Power MOSFET

Features

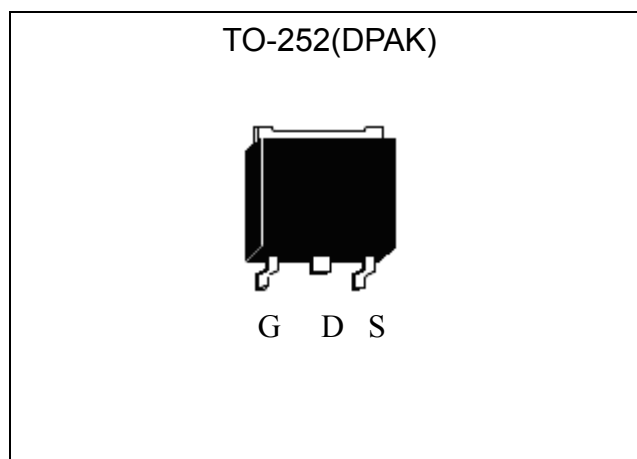
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package

BV_{DSS}	100V
I_D@ T_C=25°C, V_{GS}=10V	33A
R_{DS(ON)}@V_{GS}=10V, I_D=25A	36mΩ (typ)
R_{DS(ON)}@V_{GS}=5V, I_D=25A	38mΩ (typ)
R_{DS(ON)}@V_{GS}=4.5V, I_D=25A	39mΩ (typ)

Symbol

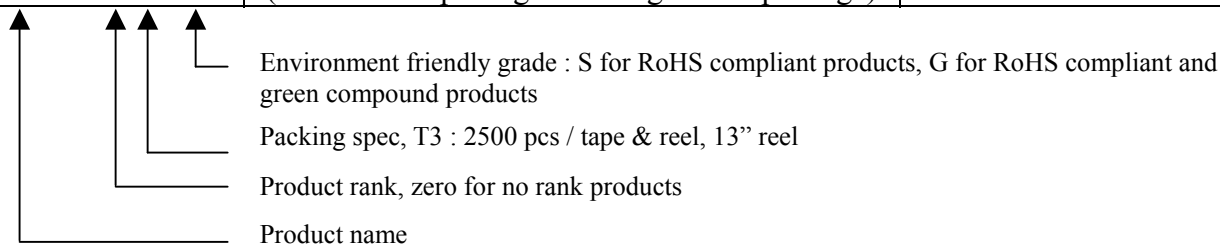


Outline



Ordering Information

Device	Package	Shipping
MTE9240J3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (T_c=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ T _c =25°C, V _{GS} =10V	I _D	33	A
Continuous Drain Current @ T _c =100°C, V _{GS} =10V		23	
Pulsed Drain Current (Note 1)	I _{DM}	90	
Avalanche Current	I _{AS}	32	mJ
Avalanche Energy @ L=0.3mH, I _D =32A, R _G =25Ω	E _{AS}	154	
Repetitive Avalanche Energy @ L=0.05mH (Note 2)	E _{AR}	9	
Total Power Dissipation @ T _c =25°C	P _d	115	W
Total Power Dissipation @ T _c =100°C		57.5	
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55~+175	°C

Note : 1. Pulse width limited by maximum junction temperature.
2. Duty cycle ≤ 1%.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	1.3	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{th,j-a}	50 (Note)	
		110	

Note : When mounted on the minimum pad size recommended (PCB mount).

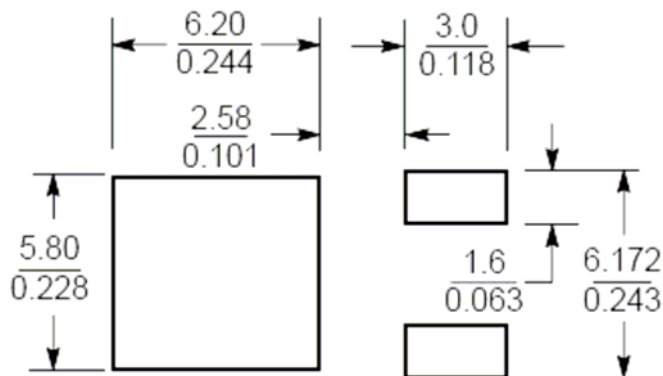
Characteristics (T_c=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	100	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1	1.4	2		V _{DS} = V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =100V, V _{GS} =0V
	-	-	25		V _{DS} =80V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	36	45	mΩ	V _{GS} =10V, I _D =25A
	-	38	45		V _{GS} =5V, I _D =25A
	-	39	50		V _{GS} =4.5V, I _D =25A
*G _{FS}	-	24	-	S	V _{DS} =10V, I _D =20A
Dynamic					
*Q _g	-	21	-	nC	V _{DS} =80V, I _D =25A, V _{GS} =10V
*Q _{gs}	-	3	-		
*Q _{gd}	-	10	-		

*Qg	-	22.7	-	nC	V _{DS} =30V, I _D =1A, V _{GS} =10V
*Qgs	-	2.9	-		
*Qgd	-	2.4	-		
*t _{d(ON)}	-	11	-	ns	V _{DS} =50V, I _D =1A, V _{GS} =10V, R _{GS} =6Ω
*tr	-	34	-		
*t _{d(OFF)}	-	62	-		
*tf	-	32	-		
Ciss	-	1180	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
Coss	-	114	-		
Crss	-	60	-		
Rg	-	3.9	-	Ω	f=1MHz
Source-Drain Diode					
*Is	-	-	33	A	
*ISM	-	-	90		
*VSD	-	0.88	1.2	V	I _F =25A, V _{GS} =0V
*trr	-	56	-	ns	I _F =25A, V _{GS} =0V, dI _F /dt=100A/μs
*Qrr	-	230	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

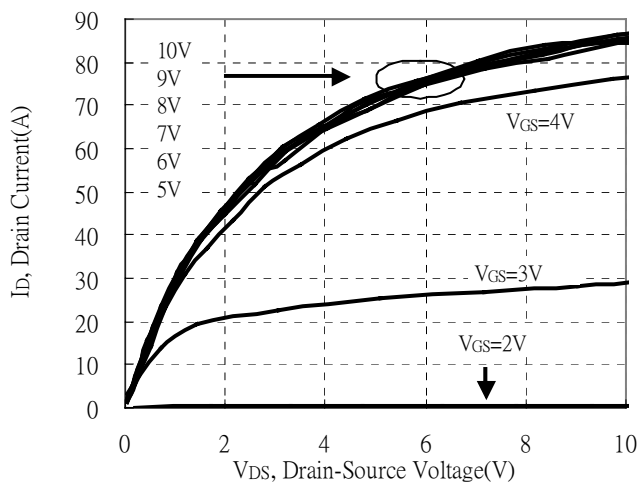
Recommended soldering footprint



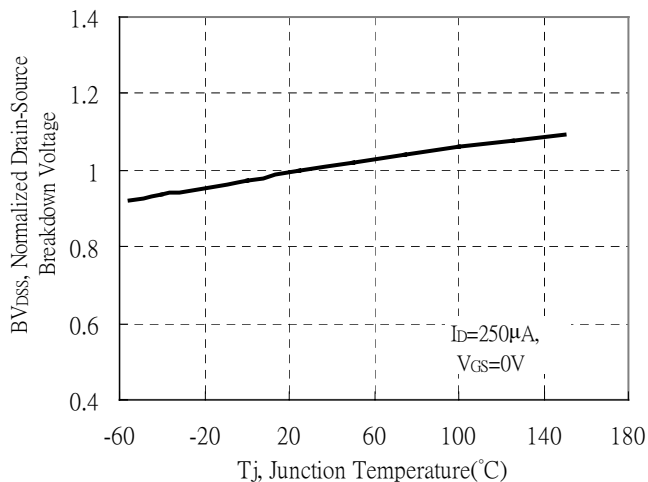
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

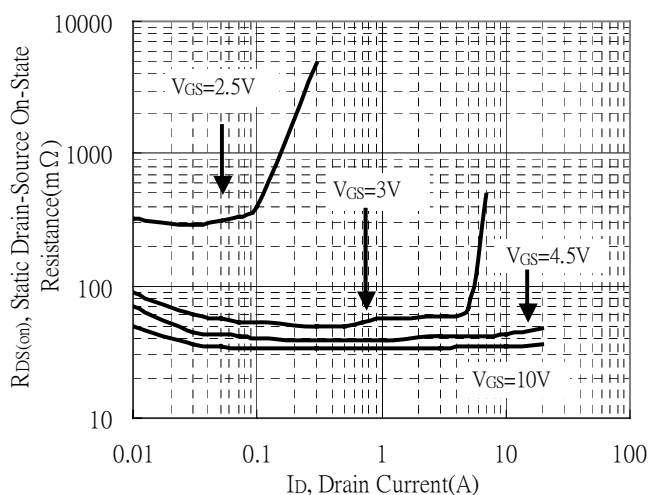
Typical Output Characteristics



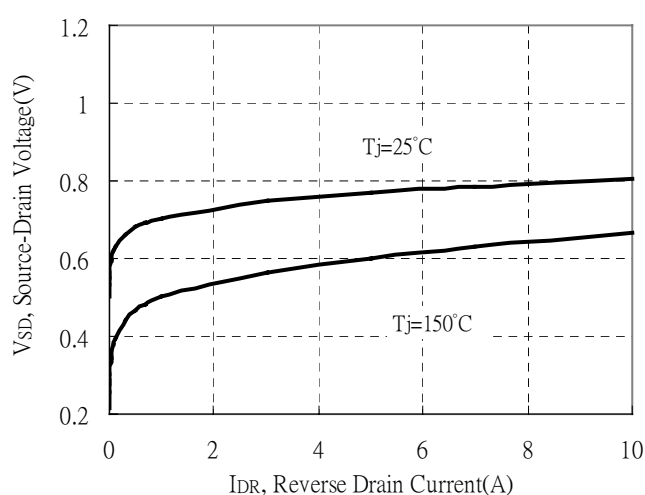
Brekdown Voltage vs Ambient Temperature



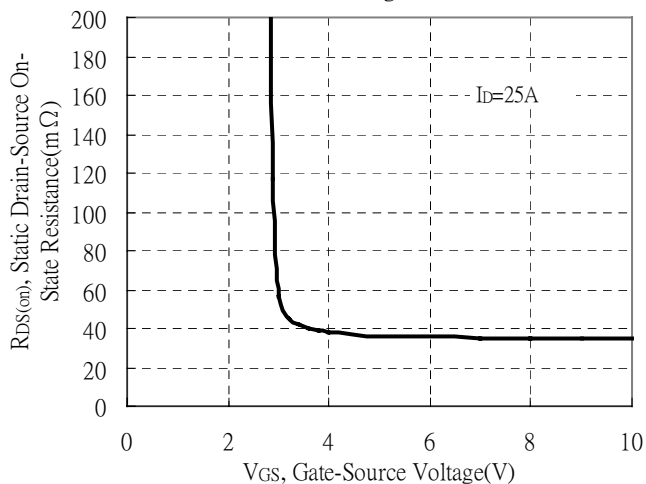
Static Drain-Source On-State resistance vs Drain Current



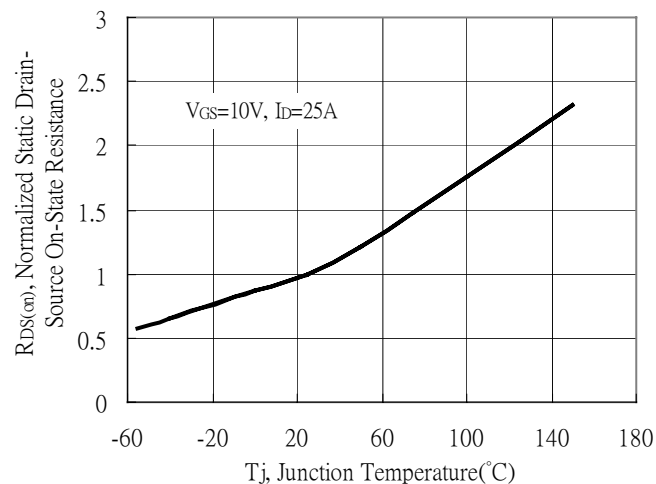
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

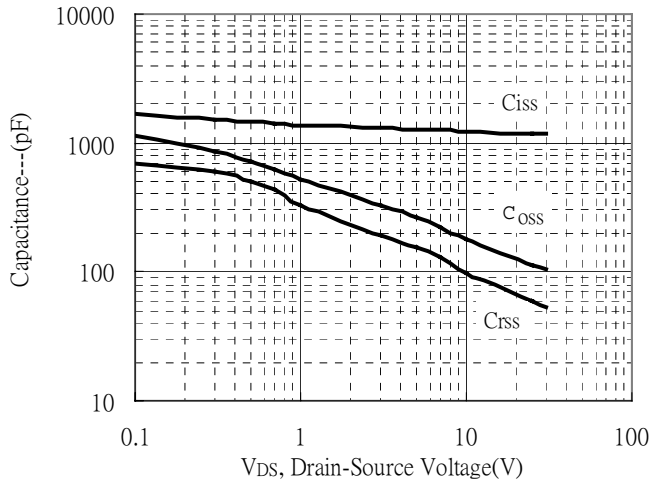


Drain-Source On-State Resistance vs Junction Temperature

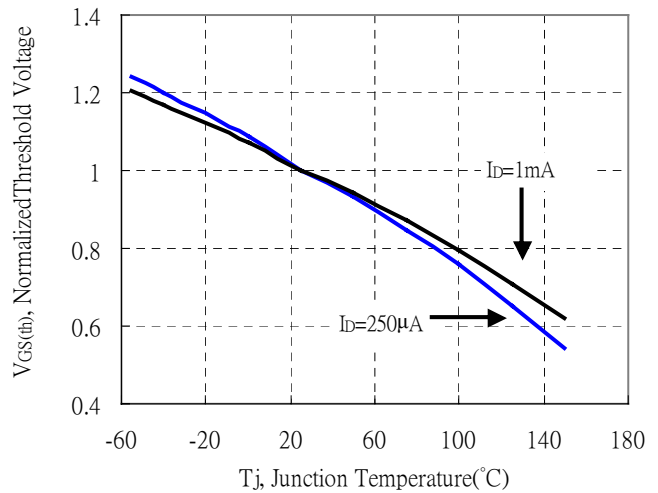


Typical Characteristics(Cont.)

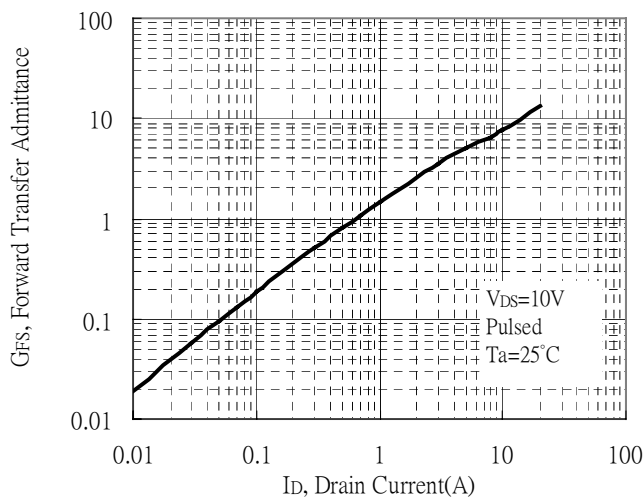
Capacitance vs Drain-to-Source Voltage



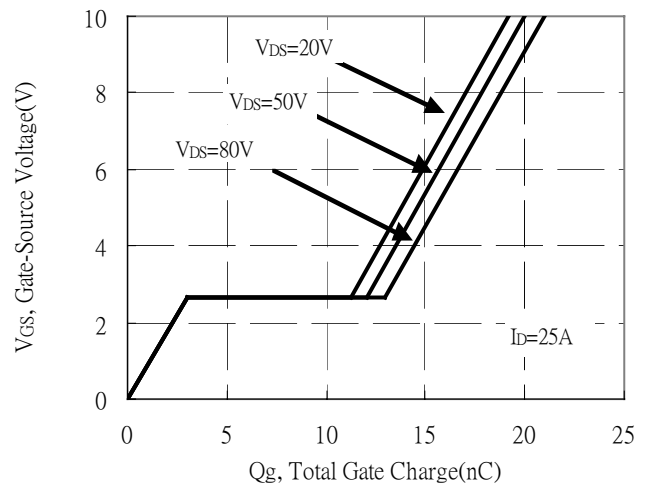
Threshold Voltage vs Junction Temperature



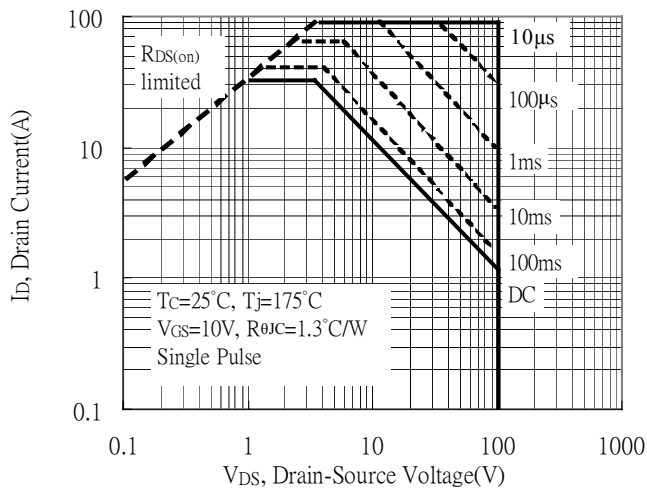
Forward Transfer Admittance vs Drain Current



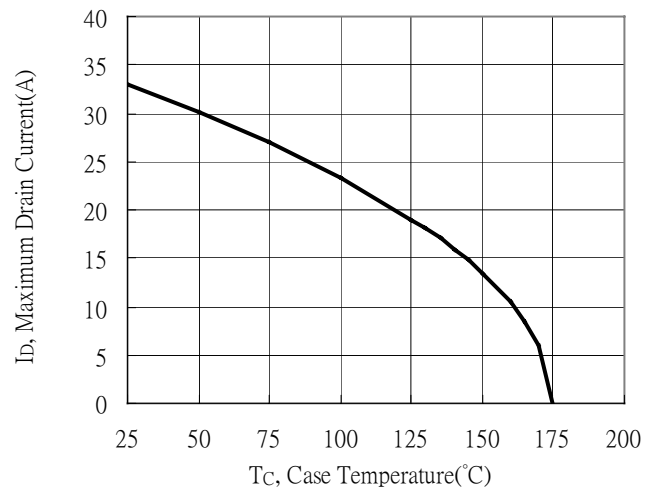
Gate Charge Characteristics



Maximum Safe Operating Area

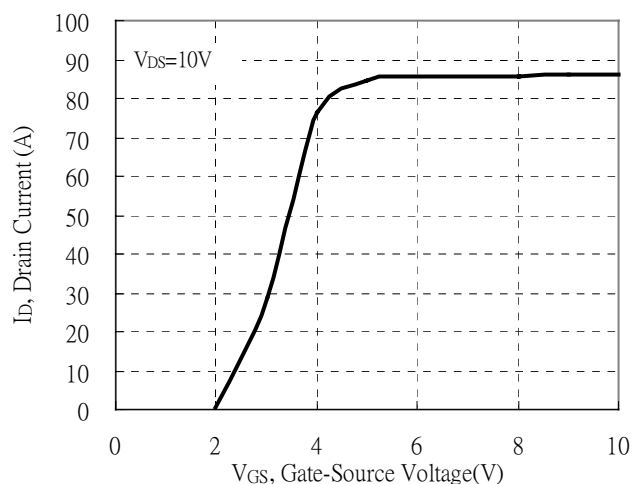


Maximum Drain Current vs Case Temperature

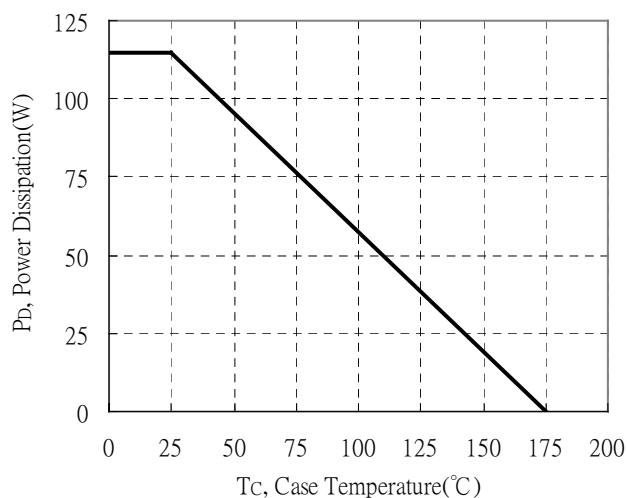


Typical Characteristics(Cont.)

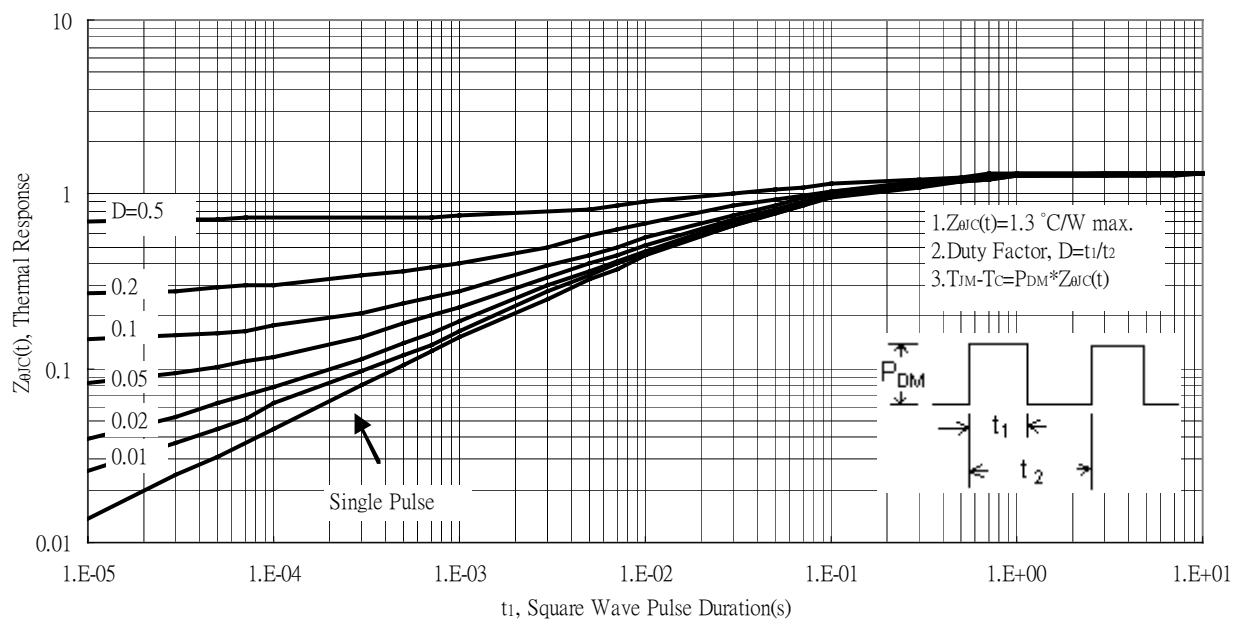
Typical Transfer Characteristics



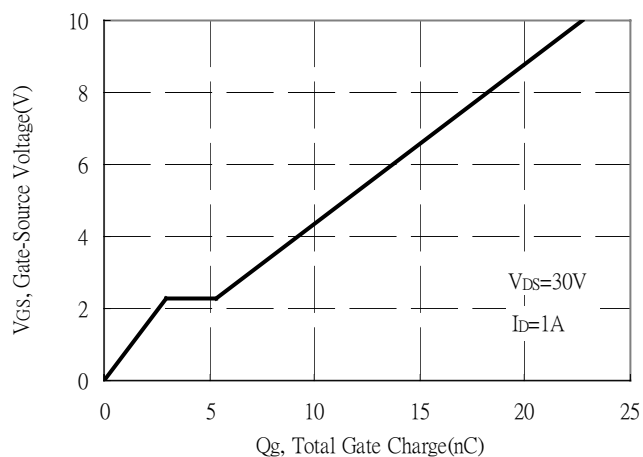
Power Derating Curve



Transient Thermal Response Curves



Gate Charge Characteristics



Technical drawing of a circular mechanical part, showing three views: front view, side view, and top view.

Front View: A circular part with a central hole. The overall diameter is 330 ± 2 mm.

Side View: Shows the thickness and internal features. The total thickness is 16.4 ± 1 mm. The distance from the bottom face to the center of the internal feature is 100 ± 1 mm. The distance from the bottom face to the top of the internal feature is 21 ± 1 mm.

Top View: Shows the circular profile with two concentric circles. The outer diameter is $\Phi 21 \pm 1$ mm and the inner diameter is $\Phi 13 \pm 1$ mm.

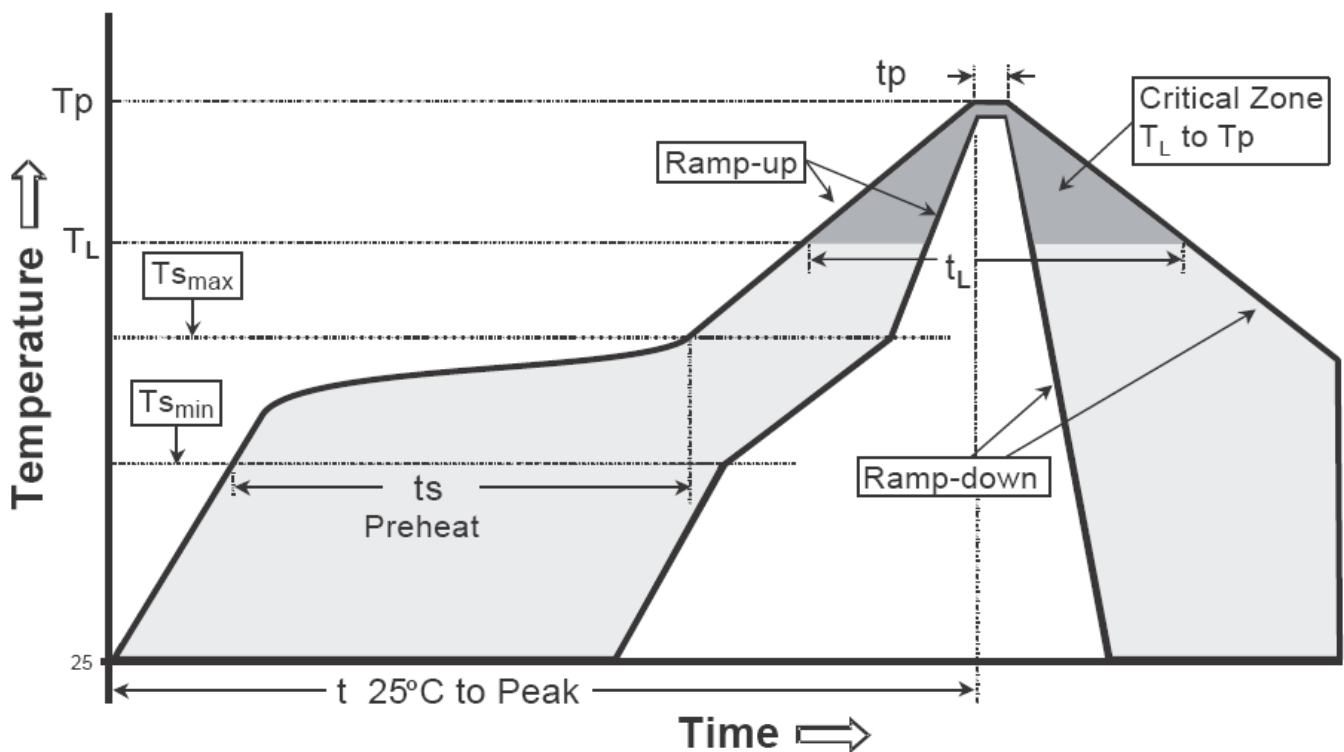
unit : mm

7

Recommended wave soldering condition

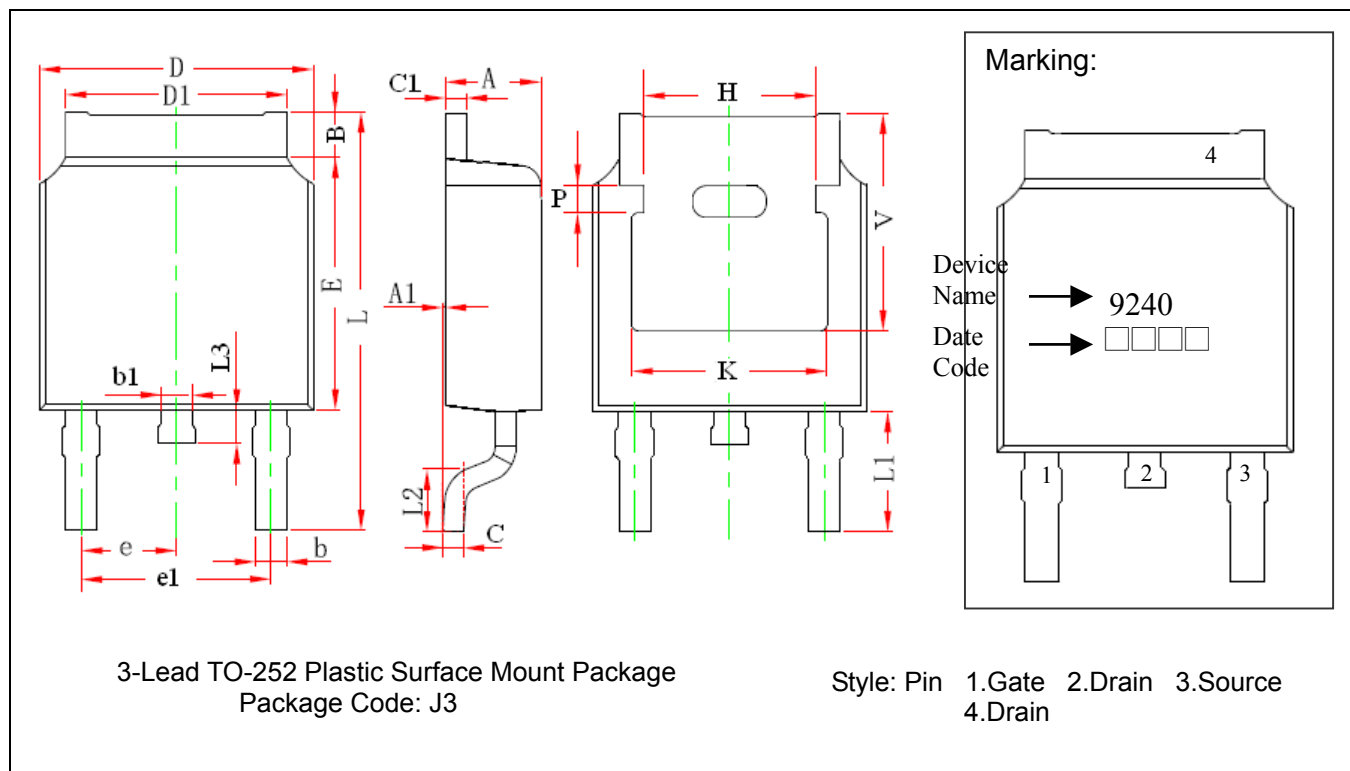
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension


DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.